



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

SURFACE MOUNT

SCHOTTKY BARRIER RECTIFIER

VOLTAGE RANGE 60 Volts CURRENT 2.0 Ampere

SMD26IGP-A

FEATURES

- * For surface mounted applications
- * Metal silicon junction, majority carrier conduction
- * Low power loss, high efficiency
- * High current capability, low forward voltage drop
- * High surge capability
- * For use in low voltage high frequency inverters, free wheeling, and polarity protection applications
- * Lead free devices

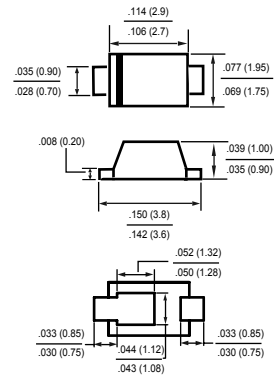
MARKING

* 26

CIRCUIT



SOD-123T



Dimensions in inches and (millimeters)

SOD-123T

MAXIMUM RATINGS (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	SMD26IGP-A	UNITS
Maximum Recurrent Peak Reverse Voltage	VRRM	60	Volts
Maximum RMS Voltage	VRMS	42	Volts
Maximum DC Blocking Voltage	VDC	60	Volts
Maximum Average Forward Rectified Current	IO	2.0	Amps
Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	IFSM	50	Amps
Typical Junction Capacitance (Note 2)	CJ	110	pF
Typical Thermal Resistance (Note 1)	RθJL	60	°C / W
Operating Temperature Range	TJ	-65 to +125	°C
Storage Temperature Range	TSTG	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	SMD26IGP-A	UNITS
Maximum Instantaneous Forward Voltage at 2.0 A DC	VF	0.65	Volts
Maximum Average Reverse Current at Rated DC Blocking Voltage	IR	500	uAmps

NOTES : 1. Thermal Resistance (Junction to Lead) : PC Board Mounted on 0.2 X 0.2" (5 X 5mm) copper pad area.
2. Measured at 1.0 MHz and applied reverse voltage of 4.0 volts.

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RATING CHARACTERISTIC CURVES (SMD26IGP-A)

FIG. 1 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

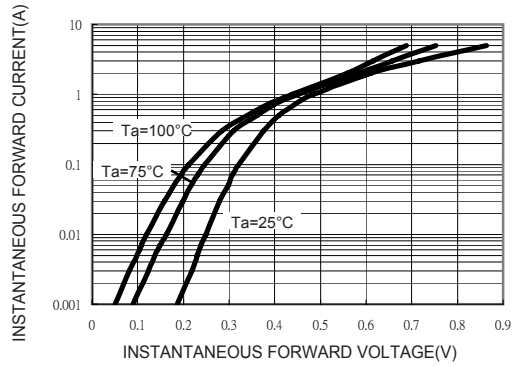


FIG. 2 - REVERSE CHARACTERISTICS

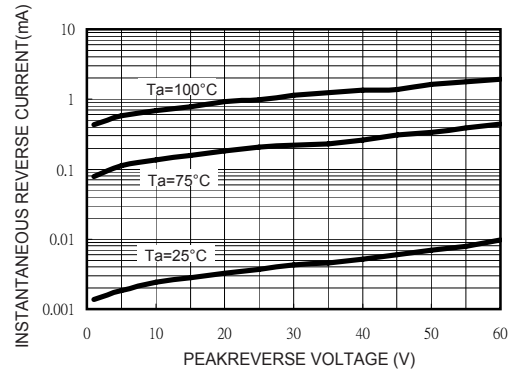


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

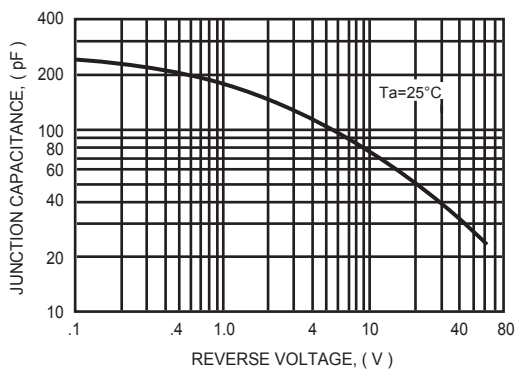


FIG. 4 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

